

a current blocking layer, formed on said second conductivity type cladding layer around said ridge portion, containing Al as a group III element in this order, wherein

an angle θ of inclination on a side surface of said ridge portion with respect to an upper surface of said substrate is at least 70° and not more than 117° ,

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(cancel)

a distance t between said emission layer and said current blocking layer satisfies a relation of $t \leq 0.275/(1 - (X2 - X1))$ micrometer assuming that $X1$ represents a composition ratio of Al in group III elements forming said second conductivity type cladding layer, $X2$ represents a composition ratio of Al in group III elements forming said current blocking layer, and

a lower width W of said ridge portion is at least $2 \mu\text{m}$ and not more than $5 \mu\text{m}$.

2. (Amended) A semiconductor laser device according to claim 1, wherein

said first conductivity type cladding layer contains Al and Ga as group III elements, and $X1$ represents a composition ratio of Al in a sum of a contents of Al and Ga, and

said current blocking layer contains Al and Ga, and III elements, and $X2$ represents the composition ratio of Al in the sum of a contents of Al and Ga.

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sub B2

4. (Amended) The semiconductor laser device according to claim 1, wherein

said distance t between said emission layer and said current blocking layer satisfies a relation of $t \leq 0.252/(1 - (X2 - X1))$ micrometer.

5. **(Amended)** The semiconductor laser device according to claim 1, wherein
said distance t between said emission layer and said current blocking layer is at least $0.15\text{ }\mu\text{m}$.

6. **(Amended)** The semiconductor laser device according to claim 1, wherein
said distance t between said emission layer and said current blocking layer is at least $0.2\text{ }\mu\text{m}$.

7. **(Amended)** The semiconductor laser device according to claim 1, wherein
an upper surface of said substrate is a $\{100\}$ plane or inclined by several degrees, and said ridge
portion extends in a $\langle 011 \rangle$ direction.
